

BUL805

High voltage fast-switching NPN Power Transistor

Preliminary Data

General features

- NPN Transistor
- High voltage capability
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed
- In compliance with the 2002/93/EC European Directive

Description

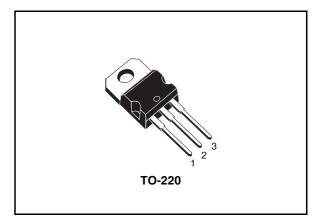
The device is manufactured using high voltage Multi-Epitaxial Planar technology for high switching speeds and medium voltage capability.

It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds.

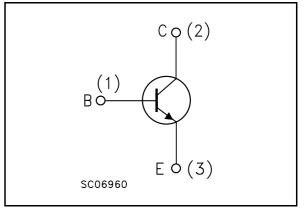
The device is designed for use as PFC in high frequency ballast half Bridge voltage fed topology.

Applications

- Electronic ballast for fluorescent lighting
- Dedicated for PFC solution in half-bridge voltage fed topology.



Internal schematic diagram



Order codes

Part Number	Marking	Package	Packing
BUL805	BUL805	TO-220	Tube

May 2006

1/8

Contents

1	Electrical ratings
2	Electrical characteristics
	2.1 Electrical characteristics (curves) 5
	2.2 Test circuits
3	Package mechanical data7
4	Revision history9



1

Electrical ratings

Table I. Absolute maximum rating	Table 1.	Absolute maximum rating	
----------------------------------	----------	-------------------------	--

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	800	V
V _{CEO}	Collector-emitter voltage ($I_B = 0$)	450	V
V _{EBO}	Emitter-base voltage (I _C = 0)	9	V
۱ _C	Collector current	5	А
I _{СМ}	Collector peak current (t _P < 5ms)	10	А
۱ _B	Base current	2	А
I _{BM}	Base peak current (t _P < 5ms)	4	А
P _{tot}	Total dissipation at $T_c = 25^{\circ}C$	80	W
T _{stg}	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	1.56	°C/W
R _{thj-amb}	Thermal resistance junction-amb max	62.5	°C/W



2 Electrical characteristics

($T_{case} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Co	onditions	Min.	Тур.	Max.	Unit
ICES	Collector cut-off current (V _{BE} =-1.5V)	V _{CE} =800V V _{CE} =800V	T _j =125°C			100 500	μΑ μΑ
I _{CEO}	Collector cut-off current (I _B =0)	V _{CE} =450V				250	μA
V _{EBO}	Emitter-base voltage (I _C = 0)	I _E =10mA		9			v
V _{CEO(sus)} ⁽¹⁾	Collector-emitter sustaining voltage (I _B = 0)	I _C =100mA	L =25mH	450			v
		I _C =1A	I _B =0.2A			0.4	V
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C =2A	I _B =0.4A			0.6	V
	outer allow voltage	I _C =3A	I _B =0.6A			0.8	V
		I _C =1A	I _B =0.2A			1.1	V
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	I _C =2A	I _B =0.4A			1.3	V
		I _C =3A	I _B =0.6A			1.5	V
h	DC ourrent agin	I _C =10mA	V _{CE} =5V	10			
h _{FE}	DC current gain	I _C =2A	V _{CE} =5V	10		20	

Table 3.	Electrical characteristics
----------	----------------------------

Note (1) Pulsed duration = $300\mu s$, duty cycle $\leq 1.5\%$



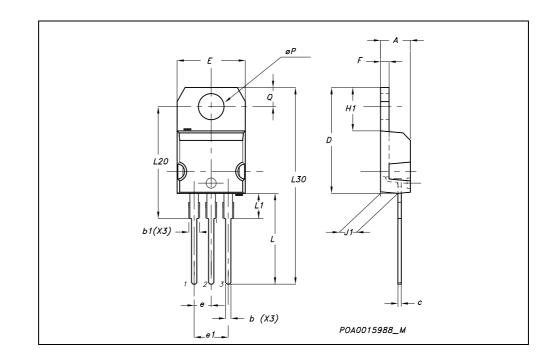
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



DIM.		mm.		inch			
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.	
А	4.40		4.60	0.173		0.181	
b	0.61		0.88	0.024		0.034	
b1	1.15		1.70	0.045		0.066	
С	0.49		0.70	0.019		0.027	
D	15.25		15.75	0.60		0.620	
Е	10		10.40	0.393		0.409	
е	2.40		2.70	0.094		0.106	
e1	4.95		5.15	0.194		0.202	
F	1.23		1.32	0.048		0.052	
H1	6.20		6.60	0.244		0.256	
J1	2.40		2.72	0.094		0.107	
L	13		14	0.511		0.551	
L1	3.50		3.93	0.137		0.154	
L20		16.40			0.645		
L30		28.90			1.137		
øP	3.75		3.85	0.147		0.151	
Q	2.65		2.95	0.104		0.116	





4 Revision history

Table 4.	Revision	history
----------	----------	---------

Date	Revision	Changes
19-May-2006	1	Initial release.



Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZE REPRESENTATIVE OF ST, ST PRODUCTS ARE NOT DESIGNED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS, WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2006 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

8/8

